L Number	Hits	Search Text	DB	Time stamp
1 .	520	(CMP or polishing) with (slurry and water)	EPO; JPO;	2004/08/23 09:19
		(com or ponoming) man (court) and maner,	DERWENT;	
			IBM_TDB	
2	1075183	semiconductor or "integrated circuit"	EPO; JPO;	2004/08/23 09:19
-			DERWENT;	
			IBM_TDB	
3	249	((CMP or polishing) with (slurry and water)) and	EPO; JPO;	2004/08/23 09:24
		(semiconductor or "integrated circuit")	DERWENT;	
		1	IBM_TDB	
4	24	438/for.111.ccls.	EPO; JPO;	2004/08/23 09:24
			DERWENT;	
_		(C) 4D 13 1 2	IBM_TDB	2004/08/22 00:24
5	1	((CMP or polishing) with (slurry and water)) and	EPO; JPO; DERWENT;	2004/08/23 09:24
		438/for.111.ccls.	IBM_TDB	
	1906	438/692.ccls.	USPAT;	2004/08/19 11:21
-	1906	430/092.CCIS.	US-PGPUB	2004/00/19 11.21
	2943	(CMP or polishing) with (slurry and water)	USPAT;	2004/08/23 09:18
-	2343	Com or policining, that (sium) and trace)	US-PGPUB	
_	447	438/692.ccls. and ((CMP or polishing) with (slurry and water))	USPAT;	2004/08/19 10:41
	• • •		US-PGPUB	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,
-	439	(438/692.ccls. and ((CMP or polishing) with (slurry and water)))	USPAT;	2004/08/19 10:45
İ		not (@ad>20030901) or @rlad>20030901)	US-PGPUB	
-	1835	(CMP or polishing) with (slurry with water)	USPAT;	2004/08/19 10:47
			US-PGPUB	
-	295	438/692.ccls. and ((CMP or polishing) with (slurry with water))	USPAT;	2004/08/19 10:47
			US-PGPUB	
-	291	(438/692.ccls. and ((CMP or polishing) with (slurry with	USPAT;	2004/08/19 11:10
[704700	water))) not (@ad>20030901 or @rlad>20030901)	US-PGPUB	0004/00/40 44.44
-	761790	dielectric or insulator or oxide or IMD or FSG or USG or TEOS	USPAT;	2004/08/19 11:11
	451	((CMP or polishing) with (slurry with water)) with (dielectric or	US-PGPUB USPAT;	2004/08/19 11:23
-	451	insulator or oxide or IMD or FSG or USG or TEOS)	US-PGPUB	2004/00/19 11.23
_	65	438/692.ccls. and (((CMP or polishing) with (slurry with water))	USPAT;	2004/08/19 11:11
_	00	with (dielectric or insulator or oxide or IMD or FSG or USG or	US-PGPUB	
		TEOS))		
-	65	(438/692.ccls. and (((CMP or polishing) with (slurry with	USPAT;	2004/08/19 11:11
		water)) with (dielectric or insulator or oxide or IMD or FSG or	US-PGPUB	
		USG or TEOS))) not (@ad>20030901 or @rlad>20030901)		
-	190	438/750.ccls.	USPAT;	2004/08/19 11:21
	-		US-PGPUB	0004/00/40 44 00
-	0		USPAT;	2004/08/19 11:22
		insulator or oxide or IMD or FSG or USG or TEOS)) with	US-PGPUB	
	357	438/750.ccls. 438/756.ccls.	USPAT;	2004/08/19 11:21
-	307	430//30.0018.	US-PGPUB	2004/00/18 11.21
_	0	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:21
	3	insulator or oxide or IMD or FSG or USG or TEOS)) with	US-PGPUB	
		438/756.ccls.		
- '	0	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:22
]		insulator or oxide or IMD or FSG or USG or TEOS)) same	US-PGPUB	
		438/750.ccls.		
-	0	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:22
		insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
	04000	438/750.ccls.	LICDAT.	2004/00/40 44:00
-	81620	438/\$.ccls.	USPAT;	2004/08/19 11:23
	404	(((CMP or poliching) with (clurp; with water)) with (dialoctic or	US-PGPUB	2004/09/40 44:22
-	121	(((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and	USPAT; US-PGPUB	2004/08/19 11:23
		11301ator of oxide of find of PSG of OSG of TEOS)) and 438/\$.ccls.	30-1 OI OB	
_	118	((((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:23
		insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
		438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)		

-	53	(((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or oxide or IMD or FSG or USG or TEOS)) and	USPAT; US-PGPUB	2004/08/19 11:30
ļ	1	438/\$.ccls.) not (@ad>20030901 or @rlad>20030901)) not	03-1 31 05	
į		((438/692.ccls. and (((CMP or polishing) with (slurry with		
		water)) with (dielectric or insulator or oxide or IMD or FSG or		
		USG or TEOS))) not (@ad>20030901 or @rlad>20030901))		
-	517047	semiconductor or "integrated circuit"	USPAT; US-PGPUB	2004/08/19 11:30
_	343	(((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:31
-	343	insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	200-1700710 11.01
		(semiconductor or "integrated circuit")		
-	293	((((CMP or polishing) with (slurry with water)) with (dielectric or	USPAT;	2004/08/19 11:31
		insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	
		(semiconductor or "integrated circuit")) not (((((CMP or polishing) with (slurry with water)) with (dielectric or insulator or		
		oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not		
		(@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and		
		(((CMP or polishing) with (slurry with water)) with (dielectric or		
		insulator or oxide or IMD or FSG or USG or TEOS))) not		
	237	(@ad>20030901 or @rlad>20030901))) (((((CMP or polishing) with (slurry with water)) with (dielectric	USPAT:	2004/08/19 11:59
-	25,	or insulator or oxide or IMD or FSG or USG or TEOS)) and	US-PGPUB	2004/00/10 11:00
		(semiconductor or "integrated circuit")) not (((((CMP or		
		polishing) with (slurry with water)) with (dielectric or insulator or		
		oxide or IMD or FSG or USG or TEOS)) and 438/\$.ccls.) not		
		(@ad>20030901 or @rlad>20030901)) not ((438/692.ccls. and (((CMP or polishing) with (slurry with water)) with (dielectric or		
		insulator or oxide or IMD or FSG or USG or TEOS))) not		
		(@ad>20030901 or @rlad>20030901)))) not ((438/692.ccls.		
1		and (((CMP or polishing) with (slurry with water)) with		
		(dielectric or insulator or oxide or IMD or FSG or USG or		
_	990	TEOS))) not (@ad>20030901 or @rlad>20030901)) "first polishing" and "second polishing"	USPAT;	2004/08/19 12:00
		mot ponotining and bootine ponotining	US-PGPUB	
-	235	((CMP or polishing) with (slurry with water)) and ("first	USPAT;	2004/08/19 12:00
	220	polishing" and "second polishing")	US-PGPUB	2004/00/40 42:00
-	229	(((CMP or polishing) with (slurry with water)) and ("first polishing" and "second polishing")) not (@ad>20030901 or	USPAT; US-PGPUB	2004/08/19 12:00
		@rlad>20030901)	0010.00	
-	206	(semiconductor or "integrated circuit") and ((((CMP or	USPAT;	2004/08/19 12:00
		polishing) with (slurry with water)) and ("first polishing" and	US-PGPUB	
		"second polishing")) not (@ad>20030901 or @rlad>20030901))		
_	29	("first polishing" with slurry) and ("second polishing" with	USPAT:	2004/08/19 12:01
		water)	US-PGPUB	
-	28	(("first polishing" with slurry) and ("second polishing" with	USPAT;	2004/08/19 12:01
	120	water)) not (@ad>20030901 or @rlad>20030901) damascene and (IMD with (FSG or USG or TEOS))	US-PGPUB	2004/09/20 11:27
-	139	damascene and (IMD with (FSG or USG of TEOS))	USPAT; US-PGPUB	2004/08/20 11:37
_	56874	@ad>20030901 or @rlad>20030901	USPAT;	2004/08/20 11:37
			US-PGPUB	
-	138	(damascene and (IMD with (FSG or USG or TEOS))) not	USPAT;	2004/08/20 11:37
	260	(@ad>20030901 or @rlad>20030901) IMD with (CMP or polishing)	US-PGPUB USPAT;	2004/08/20 11:37
_	200	Man with Come of polishing)	US-PGPUB	2007/00/20 11.3/
-	45	((damascene and (IMD with (FSG or USG or TEOS))) not	USPAT;	2004/08/21 13:48
		(@ad>20030901 or @rlad>20030901)) and (IMD with (CMP or	US-PGPUB	
	_	polishing))	LICDAT	2004/09/24 42:40
-	1	("6255201").PN.	USPAT; US-PGPUB	2004/08/21 13:48
 .	1			